

Product Overview

NGTB30N60FLWG: IGBT, 600 V, 30 A, FS1 Solar/UPS

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss.

Features

- Low Saturation Voltage using Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 5 μ s Short Circuit Capability

Benefits

- Reduces System Power Dissipation

Applications

- Solar Inverters
- Uninterruptible Power Supplies(UPS)

For more information please contact your local sales support at www.onsemi.com.

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